Fernando A. Ponce

List of Publications by Year
in descending order

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354	13,122	32410	33145
papers	citations	55 h-index	104 g-index

357	357	357	8509
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Realizing crack-free high-aluminum-mole-fraction AlGaN on patterned GaN beyond the critical layer thickness. Journal of Applied Physics, 2022, 131, .	1.1	5
2	Nanostructured materials for high efficiency solar cells. , 2021, , 201-227.		1
3	The impact of interfacial Si contamination on GaN-on-GaN regrowth for high power vertical devices. Applied Physics Letters, 2021, 118, .	1.5	14
4	Selective area regrowth and doping for vertical gallium nitride power devices: Materials challenges and recent progress. Materials Today, 2021, 49, 296-323.	8.3	21
5	Characterization of MOCVD regrown p-GaN and the interface properties for vertical GaN power devices. Semiconductor Science and Technology, 2021, 36, 014005.	1.0	3
6	High Voltage Vertical GaN p-n Diodes With Hydrogen-Plasma Based Guard Rings. IEEE Electron Device Letters, 2020, 41, 127-130.	2.2	49
7	Demonstration of GaN-based metalâ€“insulatorâ€“semiconductor junction by hydrogen plasma treatment. Applied Physics Letters, 2020, 117, .	1.5	7
8	GaN Vertical-Channel Junction Field-Effect Transistors With Regrown p-GaN by MOCVD. IEEE Transactions on Electron Devices, 2020, 67, 3972-3977.	1.6	25
9	The effect of low-angle off-axis GaN substrate orientation on the surface morphology of Mg-doped GaN epilayers. Journal of Applied Physics, 2020, 128, 055301.	1.1	1
10	Lateral and vertical growth of Mg-doped GaN on trench-patterned GaN films. Applied Physics Letters, 2020, 117, .	1.5	14
11	Influence of substrate misorientation on the optical properties of Mg-doped GaN. Journal of Applied Physics, 2020, 127, .	1.1	3
12	Investigation of polycrystalline GaxIn1â€‰â€’â€‰xP for potential use as a solar cell absorber with tunable bandgap. Journal of Applied Physics, 2020, 127, 073102.	1.1	3
13	Corrections to â€œLateral Current Spreading in III-N Ultraviolet Vertical-Cavity Surface-Emitting Lasers Using Modulation-Doped Short Period Superlatticesâ€•[Aug 18 Art. no. 2400507]. IEEE Journal of Quantum Electronics, 2019, 55, 1-1.	1.0	1
14	Dopant profiling in p-i-n GaN structures using secondary electrons. Journal of Applied Physics, 2019, 126, .	1.1	19
15	Evaluating the performance of InGaN/GaN multi-quantum-well solar cells operated at elevated temperatures via DC and small-signal AC analysis. Japanese Journal of Applied Physics, 2019, 58, 101003.	0.8	2
16	Identification of point defects using high-resolution electron energy loss spectroscopy. Physical Review B, 2019, 99, .	1.1	6
17	Non-uniform Mg distribution in GaN epilayers grown on mesa structures for applications in GaN power electronics. Applied Physics Letters, 2019, 114, .	1.5	25
18	Novel semiconductors for sustainable solar energy technologies. Journal of Physics: Conference Series, 2019, 1173, 012001.	0.3	2

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19	Implantation-and etching-free high voltage vertical GaN pâ€“n diodes terminated by plasma-hydrogenated p-GaN: revealing the role of thermal annealing. Applied Physics Express, 2019, 12, 051015.	1.1	28
20	Effect of InAs quantum dots capped with GaAs on atomic-scale ordering in Ga0.5In0.5P. Journal of Applied Physics, 2019, 125, 053104.	1.1	2
21	Determination of electronic band structure by electron holography of etched-and-regrown interfaces in GaN p-i-n diodes. Applied Physics Letters, 2019, 115, .	1.5	12
22	Investigation of GaN-on-GaN vertical p-n diode with regrown p-GaN by metalorganic chemical vapor deposition. Applied Physics Letters, 2018, 113, .	1.5	52
23	Nonpolar vertical GaN-on-GaN pâ€“n diodes grown on free-standing $(10ar{1}0)$ m-plane GaN substrates. Applied Physics Express, 2018, 11, 111003.	1.1	13
24	Theory and Design of Electron Blocking Layers for III-N-Based Laser Diodes by Numerical Simulation. IEEE Journal of Quantum Electronics, 2018, 54, 1-11.	1.0	13
25	High Resolution EELS of Point Defects in a Nitride Semiconductor Material. Microscopy and Microanalysis, 2018, 24, 430-431.	0.2	0
26	Dislocation baskets in thick InxGa1â^'xN epilayers. Journal of Applied Physics, 2018, 124, .	1.1	3
27	CdCl2 passivation of polycrystalline CdMgTe and CdZnTe absorbers for tandem photovoltaic cells. Journal of Applied Physics, 2018, 123, .	1.1	26
28	Lateral Current Spreading in III-N Ultraviolet Vertical-Cavity Surface-Emitting Lasers Using Modulation-Doped Short Period Superlattices. IEEE Journal of Quantum Electronics, 2018, 54, 1-7.	1.0	16
29	100â€nm thick singleâ€phase wurtzite BAlN films with boron contents over 10%. Physica Status Solidi (B): Basic Research, 2017, 254, 1600699.	0.7	35
30	Sub 250â€‰nm deep-UV AlGaN/AlN distributed Bragg reflectors. Applied Physics Letters, 2017, 110, .	1.5	29
31	Origin of high hole concentrations in Mgâ€doped GaN films. Physica Status Solidi (B): Basic Research, 2017, 254, 1600668.	0.7	17
32	Plasticity and optical properties of GaN under highly localized nanoindentation stress fields. Journal of Applied Physics, 2017, 121, .	1.1	28
33	Correlation between size distribution and luminescence properties of spool-shaped InAs quantum dots. Semiconductor Science and Technology, 2017, 32, 055013.	1.0	5
34	Refractory In$_{x}$ Ga1â^'$_{x}$ N Solar Cells for High-Temperature Applications. IEEE Journal of Photovoltaics, 2017, 7, 1646-1652.	1.5	26
35	Crystal structure and composition of BAlN thin films: Effect of boron concentration in the gas flow. Journal of Crystal Growth, 2017, 475, 334-340.	0.7	17
36	Stability of alloyed and nonalloyed ohmic contacts to n-type GaN at high temperature in air. Japanese Journal of Applied Physics, 2017, 56, 126502.	0.8	1

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37	A review of the synthesis of reduced defect density InxGa1â^'xN for all indium compositions. Solid-State Electronics, 2017, 136, 3-11.	0.8	19
38	High Reflectivity Hybrid AlGaN/Silver Distributed Bragg Reflectors for Use in the UV-Visible Spectrum. IEEE Journal of Quantum Electronics, 2017, 53, 1-8.	1.0	6
39	Growth and Characterization of III-N Ultraviolet Lasers and Avalanche Photodiodes by MOCVD. , 2017, , .		0
40	Local Strain Relaxation by A-type Dislocation Clusters in InxGal-xN/GaN Film with Indium Compositions of x = 0.07 and 0.12. Microscopy and Microanalysis, 2016, 22, 1572-1573.	0.2	0
41	Critical thickness investigation of MBE-grown GaInAs/GaAs and GaAsSb/GaAs heterostructures. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 02L113.	0.6	11
42	Improved optical properties of InAs quantum dots for intermediate band solar cells by suppression of misfit strain relaxation. Journal of Applied Physics, 2016, 120, .	1.1	15
43	Development of a high-band gap high temperature III-nitride solar cell for integration with concentrated solar power technology. , 2016, , .		9
44	Strain management of AlGaN-based distributed Bragg reflectors with GaN interlayer grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2016, 109, .	1.5	14
45	AlGaSb based solar cells grown on GaAs by Molecular Beam Epitaxy. , 2016, , .		0
46	Optically pumped vertical-cavity surface-emitting laser at 374.9 nm with an electrically conducting n-type distributed Bragg reflector. Applied Physics Express, 2016, 9, 111002.	1.1	21
47	Temperature Dependence and High-Temperature Stability of the Annealed Ni/Au Ohmic Contact to p-Type GaN in Air. Journal of Electronic Materials, 2016, 45, 2087-2091.	1.0	10
48	Electrically conducting n-type AlGaN/GaN distributed Bragg reflectors grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2016, 443, 81-84.	0.7	14
49	Development for ultraviolet vertical cavity surface emitting lasers. Proceedings of SPIE, 2016, , .	0.8	3
50	Early nucleation stages of low density InAs quantum dots nucleation on GaAs by MOVPE. Journal of Crystal Growth, 2016, 434, 47-54.	0.7	6
51	A new exposure model to evaluate smoked illicit drugs in rodents: A study of crack cocaine. Journal of Pharmacological and Toxicological Methods, 2016, 77, 17-23.	0.3	8
52	Onset of deep UV surface stimulated emission from AlGaN multiple quantum wells. , 2016, , .		0
53	Growth of single-phase wurtzite BAlN with 7.2%-B contents. , 2016, , .		0
54	Growth of III-Nitrides. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 331-333.	0.8	0

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55	Effect of Group-III precursors on unintentional gallium incorporation during epitaxial growth of InAlN layers by metalorganic chemical vapor deposition. Journal of Applied Physics, 2015, 118, .	1.1	5
56	Onset of surface stimulated emission at 260â€‰nm from AlGaN multiple quantum wells. Applied Physics Letters, 2015, 107, .	1.5	24
57	Growth of highâ€quality AlN layers on sapphire substrates at relatively low temperatures by metalorganic chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2015, 252, 1089-1095.	0.7	46
58	Strain Relaxation in InAs Quantum Dots and its Suppression by Indium Flushing. Microscopy and Microanalysis, 2015, 21, 983-984.	0.2	0
59	Structural and Optical Properties of AlGaN MQWs Grown by MOCVD Using One and Two TMG Sources. Microscopy and Microanalysis, 2015, 21, 1681-1682.	0.2	0
60	High Spatial/Energy Resolution Band Gap Measurements: Delocalization and Other Effects in a Monochromated Cold FEG Nion Dedicated STEM. Microscopy and Microanalysis, 2015, 21, 657-658.	0.2	1
61	Optically pumped low-threshold UV lasers. , 2015, , .		0
62	From InAs extended monolayer flat 2D terraces to 3D islands grown on GaAs substrates. , 2015, , .		0
63	III-nitride deep UV laser on sapphire substrate. , 2015, , .		0
64	Temperature dependence of the crystalline quality of AlN layer grown on sapphire substrates by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2015, 414, 76-80.	0.7	38
65	Low-temperature growth of InGaN films over the entire composition range by MBE. Journal of Crystal Growth, 2015, 425, 115-118.	0.7	36
66	Demonstration of transverse-magnetic deep-ultraviolet stimulated emission from AlGaN multiple-quantum-well lasers grown on a sapphire substrate. Applied Physics Letters, 2015, 106, .	1.5	53
67	Inverse-Tapered p-Waveguide for Vertical Hole Transport in High-[Al] AlGaN Emitters. IEEE Photonics Technology Letters, 2015, 27, 1768-1771.	1.3	9
68	Comprehensive study of the electronic and optical behavior of highly degenerate p-type Mg-doped GaN and AlGaN. Journal of Applied Physics, 2015, 117, .	1.1	49
69	Low-threshold stimulated emission at 249â€‰nm and 256â€‰nm from AlGaN-based multiple-quantum-well lasers grown on sapphire substrates. Applied Physics Letters, 2014, 105, .	1.5	78
70	Simulations, Practical Limitations, and Novel Growth Technology for InGaN-Based Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 601-606.	1.5	28
71	(Invited) Carrier Dynamics and Photon Management for Improvement in Quantum Efficiencies of GaN-Based Visible Light-Emitting Diodes. ECS Transactions, 2014, 61, 109-116.	0.3	0
72	Optically pumped deep-ultraviolet AlGaN multi-quantum-well lasers grown by metalorganic chemical vapor deposition. , 2014, , .		3

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73	High Energy and Spatial Resolution EELS Band Gap Measurements Using a Nion Monochromated Cold Field Emission HERMES Dedicated STEM. Microscopy and Microanalysis, 2014, 20, 70-71.	0.2	2
74	Optically pumped AlGaN quantumâ€well lasers at subâ€250 nm grown by MOCVD on AlN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 258-260.	0.8	13
75	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. Journal of Crystal Growth, 2014, 388, 143-149.	0.7	44
76	InAs quantum dot growth on AlxGa1â^'xAs by metalorganic vapor phase epitaxy for intermediate band solar cells. Journal of Applied Physics, 2014, 116, .	1.1	17
77	Compositional variations in In_{0.5}Ga_{0.5}N nanorods grown by molecular beam epitaxy. Nanotechnology, 2014, 25, 215705.	1.3	9
78	Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating. Journal of Crystal Growth, 2014, 388, 137-142.	0.7	45
79	A Hybrid Concentrating Solar Thermal/ Photovoltaic System Using a High Temperature III-nitride Photovoltaic Device. , 2014, , .		0
80	Room-temperature optically pumped AlGaN-AlN multiple-quantum-well lasers operating at <260nm grown by metalorganic chemical vapor deposition. Proceedings of SPIE, 2013, , .	0.8	1
81	Deep-ultraviolet lasing at 243â€‰nm from photo-pumped AlGaN/AlN heterostructure on AlN substrate. Applied Physics Letters, 2013, 102, .	1.5	77
82	Sub-250â€‰nm low-threshold deep-ultraviolet AlGaN-based heterostructure laser employing HfO2/SiO2 dielectric mirrors. Applied Physics Letters, 2013, 103, .	1.5	36
83	Highly luminescent, high-indium-content InGaN film with uniform composition and full misfit-strain relaxation. Applied Physics Letters, 2013, 103, .	1.5	35
84	Improved Hole Transport by ${m p}hbox{-}{m In}_{x}{m Ga}_{1-x}{m N}$ Layer in Multiple Quantum Wells of Visible LEDs. IEEE Photonics Technology Letters, 2013, 25, 1789-1792.	1.3	2
85	The effect of InGaN underlayers on the electronic and optical properties of InGaN/GaN quantum wells. Applied Physics Letters, 2013, 102, .	1.5	19
86	The growth of In0.5Ga0.5N and InN layers on (111)Si using nanorod intermediate arrays. Journal of Crystal Growth, 2013, 384, 55-60.	0.7	2
87	Indium Nitride and Indium Gallium Nitride layers grown on nanorods. Journal of Physics: Conference Series, 2013, 471, 012025.	0.3	1
88	Capacitance Voltage Characteristics and Electron Holography on Cubic AlGaN/GaN Heterojunctions. Japanese Journal of Applied Physics, 2013, 52, 08JN04.	0.8	9
89	The effect of nanoscratching direction on the plastic deformation and surface morphology of InP crystals. Journal of Applied Physics, 2013, 114, .	1.1	5
90	Hydrogen-related, deeply bound excitons in Mg-doped GaN films. Applied Physics Letters, 2013, 103, 082103.	1.5	12

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91	Strain-related optical properties of ZnO crystals due to nanoindentation on various surface orientations. Journal of Applied Physics, 2013, 113, 183511.	1.1	14
92	Stimulated emission at 257â€‰nm from optically-pumped AlGaN/AlN heterostructure on AlN substrate. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1768-1770.	0.8	7
93	Early stages of mechanical deformation in indium phosphide with the zinc blende structure. Journal of Applied Physics, 2012, 112, 063514.	1.1	9
94	Correlated Structural, Electronic, and Optical Properties of AlN/GaN Multiple Quantum Disks in GaN Nanowires. Applied Physics Express, 2012, 5, 025001.	1.1	6
95	Free carrier accumulation at cubic AlGaN/GaN heterojunctions. Applied Physics Letters, 2012, 100, 142108.	1.5	11
96	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .	1.5	80
97	Compositional instability in InAlN/GaN lattice-matched epitaxy. Applied Physics Letters, 2012, 100, .	1.5	30
98	Microstructure and polarization fields in nitride semiconductors. Journal of Physics: Conference Series, 2011, 326, 012001.	0.3	1
99	Microstructure of nanoscratched semiconductors. Journal of Physics: Conference Series, 2011, 326, 012061.	0.3	0
100	Plastic hardening in cubic semiconductors by nanoscratching. Journal of Applied Physics, 2011, 109, 013502.	1.1	5
101	Transmission electron microscopy study of GaInNAs(Sb) thin films grown by atomic hydrogen-assisted molecular beam epitaxy. Applied Physics Letters, 2011, 99, 191907.	1.5	14
102	Ammonothermal growth of high-quality GaN crystals on HVPE template seeds. Journal of Crystal Growth, 2011, 318, 1030-1033.	0.7	17
103	Electrostatic energy profiles at nanometerâ€scale in group III nitride semiconductors using electron holography. Annalen Der Physik, 2011, 523, 75-86.	0.9	13
104	Performance characteristics of InAlGaN laser diodes depending on electron blocking layer and waveguiding layer design grown by metalorganic chemical vapordeposition. Journal of Crystal Growth, 2011, 315, 272-277.	0.7	8
105	Optimization of growth conditions for InGaAs/InAlAs/InP quantum cascade lasers by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2011, 316, 75-80.	0.7	24
106	High quality a-plane GaN films grown on cone-shaped patterned r-plane sapphire substrates. Thin Solid Films, 2011, 519, 2508-2512.	0.8	9
107	Reduction of structural defects in a-plane GaN epitaxy by use of periodic hemispherical patterns in r-plane sapphire substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 021005.	0.6	2
108	Effect of misfit dislocations on luminescence in m-plane InGaN quantum wells. Applied Physics Letters, 2011, 98, 261914.	1.5	15

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109	Performance improvement of InGaN-based laser diodes by epitaxial layer structure design. Proceedings of SPIE, 2010, , .	0.8	3
110	Inâ€plane polarization of GaNâ€based heterostructures with arbitrary crystal orientation. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2226-2232.	0.8	19
111	Polarization effects in 2-DEG and 2-DHG AlGaN/AlN/GaN multi-heterostructures measured by electron holography. Physica Status Solidi (B): Basic Research, 2010, 247, 1722-1724.	0.7	6
112	Preface: Phys. Status Solidi C 7/1. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 7-8.	0.8	5
113	Effect of Growth Temperature on the Electron-Blocking Performance of InAlN Layers in Green Emitting Diodes. Applied Physics Express, 2010, 3, 031003.	1.1	5
114	Strain Relaxation Mechanisms in AlGaN Epitaxy on AlN Templates. Applied Physics Express, 2010, 3, 111003.	1.1	20
115	Growth of linearly ordered arrays of InAs nanocrystals on scratched InP. Journal of Applied Physics, 2010, 107, 054313.	1.1	5
116	Improvement of peak quantum efficiency and efficiency droop in III-nitride visible light-emitting diodes with an InAlN electron-blocking layer. Applied Physics Letters, 2010, 96, .	1.5	183
117	Carrier localization and nonradiative recombination in yellow emitting InGaN quantum wells. Applied Physics Letters, 2010, 96, .	1.5	52
118	Improvement of quantum efficiency by employing active-layer-friendly lattice-matched InAlN electron blocking layer in green light-emitting diodes. Applied Physics Letters, 2010, 96, .	1.5	89
119	Misfit strain relaxation in m-plane epitaxy of InGaN on ZnO. Applied Physics Letters, 2010, 96, .	1.5	6
120	Donor-related cathodoluminescence of p-AlGaN electron blocking layer embedded in ultraviolet laser diode structure. Applied Physics Letters, 2009, 94, 211103.	1.5	1
121	Nanoscale dislocation patterning by scratching in an atomic force microscope. Journal of Applied Physics, 2009, 106, 076106.	1.1	8
122	Evidence of Two-Dimensional Hole Gas in p-Type AlGaN/AlN/GaN Heterostructures. Applied Physics Express, 2009, 2, 121001.	1.1	13
123	Comparative Study on MOCVD Growth of a-Plane GaN Films on r-Plane Sapphire Substrates Using GaN, AlGaN, and AlN Buffer Layers. Journal of Electronic Materials, 2009, 38, 1938-1943.	1.0	21
124	Preface: Phys. Status Solidi A 206/2. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 193-194.	0.8	0
125	Measurement of the solubility of ammonia and nitrogen in gallium at atmospheric pressure. Journal of Alloys and Compounds, 2009, 467, 611-613.	2.8	5
126	Highly conductive modulation doped composition graded p-AlGaN/(AlN)/GaN multiheterostructures grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2009, 106, .	1.1	17

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127	SEM characterization of silicon nanostructures: can we meet the challenge?. Scanning, 2008, 30, 310-316.	0.7	5
128	Synthesis and luminescence properties of ZnO nanostructures produced by the solâ€“gel method. Journal of Crystal Growth, 2008, 310, 599-603.	0.7	64
129	Growth of free-standing highly luminescent undoped and Mg-doped GaN thick films with a columnar structure. Journal of Crystal Growth, 2008, 310, 3131-3134.	0.7	9
130	Surface morphology control of green LEDs with p-InGaN layers grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 5166-5169.	0.7	6
131	Control of quantum-confined Stark effect in InGaNâˆ•GaN multiple quantum well active region by p-type layer for III-nitride-based visible light emitting diodes. Applied Physics Letters, 2008, 92, .	1.5	60
132	Blue light emitting diodes grown on freestanding (11-20) a-plane GaN substrates. Applied Physics Letters, 2008, 92, 011123.	1.5	26
133	Time-resolved cathodoluminescence of Mg-doped GaN. Applied Physics Letters, 2008, 93, .	1.5	19
134	Effect of native oxide mechanical deformation on InP nanoindentation. Journal of Applied Physics, 2008, 104, .	1.1	10
135	Photoluminescence of near-lattice-matched GaNâˆ•AlInN quantum wells grown on free-standing GaN and on sapphire substrates. Applied Physics Letters, 2008, 92, .	1.5	7
136	Role of the buffer layer thickness on the formation of basal plane stacking faults in a-plane GaN epitaxy on r-sapphire. Applied Physics Letters, 2008, 93, 011901.	1.5	24
137	Structural and optical properties of nonpolar GaN thin films. Applied Physics Letters, 2008, 92, .	1.5	61
138	Determination of the electronic band structure for a graded modulation-doped AlGaNâˆ•AlNâˆ•GaN superlattice. Applied Physics Letters, 2007, 91, 142121.	1.5	9
139	Basal-plane slip in InGaNâˆ•GaN heterostructures in the presence of threading dislocations. Applied Physics Letters, 2007, 90, 171922.	1.5	13
140	Mapping the electrostatic potential across AlGaNâˆ•AlNâˆ•GaN heterostructures using electron holography. Applied Physics Letters, 2007, 90, 032101.	1.5	26
141	Atomic force nanolithography of InP for site control growth of InAs nanostructures. Applied Physics Letters, 2007, 90, 013117.	1.5	12
142	Effect of internal electrostatic fields in InGaN quantum wells on the properties of green light emitting diodes. Applied Physics Letters, 2007, 91, .	1.5	25
143	Optical properties of highly luminescent zinc oxide tetrapod powders. Applied Physics Letters, 2007, 91, 121905.	1.5	21
144	Metalâ€“Organic Hydride Vapor Phase Epitaxy of AlxGa1-xN Films over Sapphire. Japanese Journal of Applied Physics, 2007, 46, L752-L754.	0.8	23

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145	TEM Characterization of ZnO Crystals Synthesize with Controlled Size and Morphology. Microscopy and Microanalysis, 2007, 13, .	0.2	0
146	Synthesis of highly luminescent, undoped, Mg-doped and Si-doped GaN powders. Journal of Crystal Growth, 2007, 304, 225-232.	0.7	9
147	Dislocation generation at the coalescence of aluminum nitride lateral epitaxy on shallow-grooved sapphire substrates. Applied Physics Letters, 2007, 90, 221909.	1.5	27
148	Correlation of spectral luminescence with threading dislocations in green-light-emitting InGaN quantum wells. Applied Physics Letters, 2007, 90, 231901.	1.5	17
149	AlxGa1â^'xN (0â©½xâ©½1) nanocrystalline powder by pyrolysis route. Journal of Crystal Growth, 2007, 308, 198-203.	0.7	5
150	Growth of InAs nanostructures on InP using atomic-force nanolithography. Applied Physics A: Materials Science and Processing, 2007, 89, 945-949.	1.1	7
151	Misfit Dislocation Generation in InGaN Epilayers on Free-Standing GaN. Japanese Journal of Applied Physics, 2006, 45, L549-L551.	0.8	38
152	Pulsed lateral epitaxial overgrowth of aluminum nitride on sapphire substrates. Applied Physics Letters, 2006, 89, 081905.	1.5	79
153	Carrier dynamics and electrostatic potential variation in InGaN quantum wells grown on {112Â¯2} GaN pyramidal planes. Applied Physics Letters, 2006, 89, 231908.	1.5	10
154	Structure and luminescence of nanocrystalline gallium nitride synthesized by a novel polymer pyrolysis route. Optical Materials, 2006, 29, 19-23.	1.7	15
155	Optical Properties of GaN Nanowhiskers Produced by Photoelectrochemical Etching. ECS Transactions, 2006, 3, 415-419.	0.3	4
156	Generation of misfit dislocations by basal-plane slip in InGaNâ•GaN heterostructures. Applied Physics Letters, 2006, 89, 201911.	1.5	61
157	Prismatic stacking faults in epitaxially laterally overgrown GaN. Applied Physics Letters, 2006, 88, 141912.	1.5	69
158	Growth of InN on Ge substrate by molecular beam epitaxy. Journal of Crystal Growth, 2005, 279, 311-315.	0.7	14
159	CBED study of grain misorientations in AlGaN epilayers. Ultramicroscopy, 2005, 103, 23-32.	0.8	0
160	Influence of stacking faults on the properties of GaN-based UV light-emitting diodes grown on non-polar substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2732-2735.	0.8	11
161	Electrostatic Fields and Compositional Fluctuations in InGaN Quantum Wells. AIP Conference Proceedings, 2005, , .	0.3	1
162	The Electronic Nature of metal/p-GaN Junctions. AIP Conference Proceedings, 2005, , .	0.3	0

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163	Localization versus carrier-screening effects in InGaN quantum wells â€" A time-resolved cathodoluminescence study. AIP Conference Proceedings, 2005, , .	0.3	1
164	Crystal Structure of Low-Resistance Au-Ni/p-GaN Contacts. AIP Conference Proceedings, 2005, , .	0.3	1
165	Deep green emission at 570nm from InGaN/GaN MQW active region grown on bulk AlN substrate. , 2005, 5941, 37.		2
166	The Nature of Crystalline Defects in a-plane GaN Films. AIP Conference Proceedings, 2005, , .	0.3	0
167	Light Emission from GaN Microcrystals. AIP Conference Proceedings, 2005, , .	0.3	0
168	Optoelectronic and microstructure attributes of epitaxial SrTiO3 on Si. Journal of Applied Physics, 2005, 97, 014101.	1.1	25
169	Polychromatic light emission from single InGaN quantum wells grown on pyramidal GaN facets. Applied Physics Letters, 2005, 87, 131911.	1.5	44
170	Fine structure of AlNâˆ•AlGaN superlattice grown by pulsed atomic-layer epitaxy for dislocation filtering. Applied Physics Letters, 2005, 87, 211915.	1.5	49
171	A Novel Method to Synthesize Blue-Luminescent Doped GaN Powders. Materials Research Society Symposia Proceedings, 2005, 864, 6101.	0.1	2
172	Strain Relaxation Mechanisms in InGaN Epilayers. AIP Conference Proceedings, 2005, , .	0.3	0
173	Luminescence from stacking faults in gallium nitride. Applied Physics Letters, 2005, 86, 021908.	1.5	315
174	Nitrogen surfactant effects in GaInP. Journal of Applied Physics, 2004, 96, 7229-7234.	1.1	4
175	Epitaxial growth of AlxGa1âˆ'xN on Si(111) via a ZrB2(0001) buffer layer. Applied Physics Letters, 2004, 84, 3510-3512.	1.5	20
176	Raman line shape of the A1 longitudinal optical phonon in GaN. Applied Physics Letters, 2004, 84, 3471-3473.	1.5	13
177	The generation of misfit dislocations in facet-controlled growth of AlGaNâˆ•GaN films. Applied Physics Letters, 2004, 85, 4923-4925.	1.5	14
178	Localization versus field effects in single InGaN quantum wells. Applied Physics Letters, 2004, 84, 58-60.	1.5	36
179	Defect and stress control of AlGaN for fabrication of high performance UV light emitters. Physica Status Solidi A, 2004, 201, 2679-2685.	1.7	21
180	Atomic arrangement at the Auâˆ•p-GaN interface in low-resistance contacts. Applied Physics Letters, 2004, 85, 6143-6145.	1.5	30

#	Article	IF	Citations
181	Spatial variation of luminescence from AlGaN grown by facet controlled epitaxial lateral overgrowth. Applied Physics Letters, 2004, 85, 3417-3419.	1.5	16
182	Exciton freeze-out and thermally activated relaxation at local potential fluctuations in thick AlxGa1â^'xN layers. Journal of Applied Physics, 2004, 95, 4670-4674.	1.1	119
183	Effect of layer thickness on the electrostatic potential in InGaN quantum wells. Applied Physics Letters, 2004, 85, 4651-4653.	1.5	31
184	MOVPE growth of GaN on Si(111) substrates. Journal of Crystal Growth, 2003, 248, 556-562.	0.7	125
185	Growth of GaN on ZrB2 substrate by metal-organic vapor phase epitaxy. Applied Surface Science, 2003, 216, 502-507.	3.1	30
186	Microstructure and electronic properties of InGaN alloys. Physica Status Solidi (B): Basic Research, 2003, 240, 273-284.	0.7	131
187	Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1583-1606.	0.8	116
188	Gallium-nitride-based devices on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1940-1949.	0.8	18
189	Glide along non-basal slip planes in InGaN epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2440-2443.	0.8	3
190	Thick crack-free AlGaN films deposited by facet-controlled epitaxial lateral overgrowth. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2136-2140.	0.8	13
191	Luminescence Properties of Charged Dislocations in Semi-Insulating GaN : Zn. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 508-511.	0.8	2
192	Mechanism of H2 pre-annealing on the growth of GaN on sapphire by MOVPE. Applied Surface Science, 2003, 216, 585-589.	3.1	17
193	Atomic arrangement at the AlN/Si (111) interface. Applied Physics Letters, 2003, 83, 860-862.	1.5	114
194	Effects of Si-doping on the Microstructure of AlGaN/GaN Multiple-quantum-well. Materials Research Society Symposia Proceedings, 2003, 798, 512.	0.1	0
195	Optical and Microstructural Properties of N- and Ga-Polarity GaN. Materials Research Society Symposia Proceedings, 2003, 798, 580.	0.1	1
196	Platelet Inversion Domains Induced by Mg-doping in ELOG AlGaN Films. Materials Research Society Symposia Proceedings, 2003, 798, 478.	0.1	0
197	Slip systems and misfit dislocations in InGaN epilayers. Applied Physics Letters, 2003, 83, 5187-5189.	1.5	194
198	Structural and optical characterization of nonpolar GaN/AlN quantum wells. Applied Physics Letters, 2003, 83, 653-655.	1.5	37

#	Article	IF	Citations
199	Light emission and microstructure of Mg-doped AlGaN grown on patterned sapphire. Applied Physics Letters, 2003, 82, 349-351.	1.5	71
200	Structural and optical properties of coherent GaN islands grown on 6H-SiC(0001)-(â˜š3Ã—â˜š3). Applied Physics Letters, 2003, 82, 2889-2891.	1.5	11
201	Synthesis, Structure and Luminescence of High Brightness Gallium Nitride Powder. Materials Research Society Symposia Proceedings, 2003, 798, 243.	0.1	1
202	Study of charge distribution across interfaces in GaN/InGaN/GaN single quantum wells using electron holography. Journal of Applied Physics, 2002, 91, 9856.	1.1	47
203	Atomic arrangement at the AlN/ZrB2 interface. Applied Physics Letters, 2002, 81, 3182-3184.	1.5	27
204	Microscopic correlation of redshifted luminescence and surface defects in thick InxGa1â˜'xN layers. Applied Physics Letters, 2002, 80, 3524-3526.	1.5	21
205	Response to â€œComment on â€˜Low Stokes shift in thick and homogeneous InGaN epilayersâ€™â€Šâ€•[Appl. Phys. Lett 81, 1353 (2002)]. Applied Physics Letters, 2002, 81, 1355-1356.	1.5	1
206	Distinct Magnesium Incorporation Behavior in Laterally Grown AlGaN. Materials Research Society Symposia Proceedings, 2002, 743, L1.11.1.	0.1	1
207	Hollow core dislocations in Mg-doped AlGaN. Materials Research Society Symposia Proceedings, 2002, 743, L10.9.1.	0.1	0
208	Growth of self-assembled GaN quantum dots via the vaporâ€“liquidâ€“solid mechanism. Applied Physics Letters, 2002, 81, 3236-3238.	1.5	33
209	Dislocation annihilation by silicon delta-doping in GaN epitaxy on Si. Applied Physics Letters, 2002, 81, 4712-4714.	1.5	109
210	Low Stokes shift in thick and homogeneous InGaN epilayers. Applied Physics Letters, 2002, 80, 550-552.	1.5	58
211	Polarity determination by atomic location by channeling-enhanced microanalysis. Applied Physics Letters, 2002, 80, 389-391.	1.5	13
212	Observation of coreless edge and mixed dislocations in Mg-doped Al0.03Ga0.97N. Applied Physics Letters, 2002, 81, 4541-4543.	1.5	24
213	Microstructural properties of Eu-doped GaN luminescent powders. Applied Physics Letters, 2002, 81, 1993-1995.	1.5	29
214	Preface: phys. stat. sol. (b) 230/2/2002. Physica Status Solidi (B): Basic Research, 2002, 230, 307-308.	0.7	0
215	Electron Holography Studies of the Charge on Dislocations in GaN. Physica Status Solidi (B): Basic Research, 2002, 234, 924-930.	0.7	40
216	Bright, Crack-Free InGaN/GaN Light Emitters on Si(111). Physica Status Solidi A, 2002, 192, 308-313.	1.7	41

#	Article	IF	Citations
217	Determination by Electron Holography of the Electronic Charge Distribution at Threading Dislocations in Epitaxial GaN. Physica Status Solidi A, 2002, 192, 407-411.	1.7	42
218	Spatial variation of luminescence of InGaN alloys measured by highly-spatially-resolved scanning cathodoluminescence. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 19-23.	1.7	10
219	Low-energy electron-excited nanoluminescence studies of GaN and related materials. Applied Surface Science, 2002, 190, 498-507.	3.1	4
220	The transition from As-doped GaN, showing blue emission, to GaNAs alloys in films grown by molecular beam epitaxy. Journal of Crystal Growth, 2002, 240, 423-430.	0.7	14
221	Low energy electron-excited nano-luminescence spectroscopy of GaN surfaces and interfaces. Applied Surface Science, 2001, 175-176, 442-449.	3.1	5
222	A Comparison of Rutherford Backscattering Spectroscopy and X-Ray Diffraction to Determine the Composition of Thick InGaN Epilayers. Physica Status Solidi (B): Basic Research, 2001, 228, 41-44.	0.7	23
223	Luminescence studies of defects and piezoelectric fields in InGaN/GaN single quantum wells. Journal of Crystal Growth, 2001, 230, 481-486.	0.7	8
224	The nature of arsenic incorporation in GaN. Applied Physics Letters, 2001, 79, 3239-3241.	1.5	8
225	Spatial variation of luminescence in thick GaN films. Applied Physics Letters, 2001, 78, 1222-1224.	1.5	16
226	Edge and screw dislocations as nonradiative centers in InGaN/GaN quantum well luminescence. Applied Physics Letters, 2001, 78, 2691-2693.	1.5	218
227	Anisotropic diffusion and drift of photogenerated carriers near coreless dislocations in InGaN quantum well. Applied Physics Letters, 2001, 79, 75-77.	1.5	7
228	Profiling electric fields in GaN/InGaN/GaN single quantum wells by electron holography. Materials Research Society Symposia Proceedings, 2000, 639, 11201.	0.1	0
229	Polarity determination and atomic arrangements at a GaN/SiC interface using high-resolution image matching. Applied Physics Letters, 2000, 76, 822-824.	1.5	28
230	Mapping electrostatic potential across an AlGaN/InGaN/AlGaN diode by electron holography. Applied Physics Letters, 2000, 76, 3055-3057.	1.5	57
231	Localized states at InGaN/GaN quantum well interfaces. Applied Physics Letters, 1999, 75, 3835-3837.	1.5	41
232	Measurement of the piezoelectric field across strained InGaN/GaN layers by electron holography. Solid State Communications, 1999, 111, 281-285.	0.9	48
233	Defect formation near GaN surfaces and interfaces. Physica B: Condensed Matter, 1999, 273-274, 70-74.	1.3	25
234	Depth-resolved electron-excited nanoscale-luminescence spectroscopy studies of defects near GaN/InGaN/GaN quantum wells. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2545.	1.6	23

#	Article	IF	Citations
235	Determination of the atomic structure of inversion domain boundaries in Î±-GaN by transmission electron microscopy. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1998, 77, 273-286.	0.8	47
236	Defects and Interfaces in GaN Epitaxy. MRS Bulletin, 1997, 22, 51-57.	1.7	93
237	Amorphous Domains in GaN Layers Grown on 6H-SiC by MBE. Materials Research Society Symposia Proceedings, 1997, 482, 487.	0.1	0
238	Microstructure of InGaN Quantum Wells. Materials Research Society Symposia Proceedings, 1997, 482, 31.	0.1	22
239	Cathodoluminescence Studies of InGaN Quantum Wells. Materials Research Society Symposia Proceedings, 1997, 482, 660.	0.1	11
240	Environment About Indium in Ga_{1-x}In_xN from In and Ga K-Edge XAFS. European Physical Journal Special Topics, 1997, 7, C2-1253-C2-1254.	0.2	0
241	Observation of coreless dislocations in Î±-GaN. Journal of Crystal Growth, 1997, 178, 201-206.	0.7	87
242	Nitride-based semiconductors for blue and green light-emitting devices. Nature, 1997, 386, 351-359.	13.7	1,550
243	Characterisation of dislocations, nanopipes and inversion domains in GaN by transmission electron microscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 50, 76-81.	1.7	35
244	Homoepitaxy of GaN on polished bulk single crystals by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 68, 917-919.	1.5	107
245	Spatial distribution of the luminescence in GaN thin films. Applied Physics Letters, 1996, 68, 57-59.	1.5	361
246	Determination of lattice polarity for growth of GaN bulk single crystals and epitaxial layers. Applied Physics Letters, 1996, 69, 337-339.	1.5	227
247	Thermal Stability of Pt, Pd, and Ni on GaN. Materials Research Society Symposia Proceedings, 1996, 449, 1049.	0.1	11
248	Nanopipes and Inversion Domains in High-Quality GaN Epitaxial Layers. Materials Research Society Symposia Proceedings, 1996, 449, 405.	0.1	22
249	Characterization of OMVPE-Grown AlGaInN Heterostructures. Materials Research Society Symposia Proceedings, 1996, 449, 509.	0.1	31
250	Mapping of Donor Impurities in Gan By Raman Imaging. Materials Research Society Symposia Proceedings, 1996, 449, 731.	0.1	1
251	Atomic arrangement at the AlN/SiC interface. Physical Review B, 1996, 53, 7473-7478.	1.1	75
252	Direct imaging of impurityâ€induced Raman scattering in GaN. Applied Physics Letters, 1996, 69, 2650-2652.	1.5	71

#	Article	IF	Citations
253	Characterization of dislocations in GaN by transmission electron diffraction and microscopy techniques. Applied Physics Letters, 1996, 69, 770-772.	1.5	184
254	Transmission electron microscopy of the AlNâ€“SiC interface. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1996, 74, 777-789.	0.8	9
255	High-Quality GaN heteroepitaxial films grown by metalorganic chemical vapor deposition. Journal of Electronic Materials, 1995, 24, 257-261.	1.0	21
256	High dislocation densities in high efficiency GaNâ€based lightâ€emitting diodes. Applied Physics Letters, 1995, 66, 1249-1251.	1.5	961
257	Microstructure of GaN epitaxy on SiC using AlN buffer layers. Applied Physics Letters, 1995, 67, 410-412.	1.5	200
258	Defect generation and suppression during the impurityâ€induced layer disordering of quantumâ€sized GaAs/GaInP layers. Applied Physics Letters, 1994, 65, 2696-2698.	1.5	4
259	Selfâ€limiting oxidation for fabricating subâ€5 nm silicon nanowires. Applied Physics Letters, 1994, 64, 1383-1385.	1.5	270
260	Crystalline structure of AlGaN epitaxy on sapphire using AlN buffer layers. Applied Physics Letters, 1994, 65, 2302-2304.	1.5	140
261	Strained Ga/sub x/In/sub 1-x/P/(AlGa)/sub 0.5/In/sub 0.5/P heterostructures and quantum-well laser diodes. IEEE Journal of Quantum Electronics, 1994, 30, 593-607.	1.0	115
262	C^{â^'} Outgrowths in C⁺ Thin Films of LiNbO₃ on Al₂O₃-c. Materials Research Society Symposia Proceedings, 1994, 341, 289.	0.1	16
263	Critical thickness determination of InAs, InP and GaP on GaAs by X-ray interference effect and transmission electron microscopy. Journal of Crystal Growth, 1993, 131, 465-469.	0.7	20
264	Strain and defect generation during interdiffusion of GaAs into Al0.5In0.5P. Applied Physics Letters, 1993, 62, 2060-2062.	1.5	5
265	Experimental evidence of the structure of annihilation of antiphase boundaries in GaAs on Si. Materials Letters, 1993, 15, 353-355.	1.3	0
266	Epitaxial BaTiO3/MgO Structure Grown on GaAs(100) by Pulsed Laser Deposition*. Japanese Journal of Applied Physics, 1993, 32, 4099-4102.	0.8	57
267	Structural characterization of GaAs/GaP superlattices. Journal Physics D: Applied Physics, 1993, 26, A167-A172.	1.3	4
268	Self-limiting oxidation of Si nanowires. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 2532.	1.6	149
269	Effect of interface chemistry on the growth of ZnSe on the Si(100) surface. Physical Review B, 1992, 45, 13400-13406.	1.1	58
270	Oxidation of sub-50 nm Si columns for light emission study. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2846.	1.6	92

#	Article	IF	Citations
271	Initial Stages of Growth of ZnSe on Si. Materials Research Society Symposia Proceedings, 1992, 242, 191.	0.1	1
272	Temperature Dependent C-V Characteristics of YBCO/YSZ/Si MIS Capacitors. Materials Research Society Symposia Proceedings, 1992, 275, 583.	0.1	0
273	Silicon Quantum Wires Oxidation and Transport Studies. Materials Research Society Symposia Proceedings, 1992, 283, 57.	0.1	2
274	Thermal donor formation and annihilation in oxygenâ€implanted floatâ€zone silicon. Journal of Applied Physics, 1992, 72, 1758-1765.	1.1	9
275	Use of ZnSe as an interlayer for GaAs growth on Si. Applied Physics Letters, 1992, 61, 195-197.	1.5	24
276	Reactions at the interfaces of thin films of Yâ€Baâ€Cuâ€and Zrâ€oxides with Si substrates. Journal of Applied Physics, 1991, 69, 2176-2182.	1.1	85
277	Microstructure of Impurity Induced Disordering at The GaAs/InGaAlP Interface. Materials Research Society Symposia Proceedings, 1991, 221, 349.	0.1	1
278	Epitaxial Growth of Ferroelectric Thin Films on GaAs with MgO Buffer Layers by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 1991, 243, 495.	0.1	4
279	Hydrogen in crystalline semiconductors. Physica B: Condensed Matter, 1991, 170, 3-20.	1.3	104
280	Epitaxial MgO on Si(001) for Yâ€Baâ€Cuâ€O thinâ€film growth by pulsed laser deposition. Applied Physics Letters, 1991, 58, 2294-2296.	1.5	237
281	High critical current densities in epitaxial YBa2Cu3O7âˆ’Î´thin films on siliconâ€onâ€sapphire. Applied Physics Letters, 1991, 58, 2432-2434.	1.5	57
282	Structural aspects of silicon diffusion in quaternary III-V thin-film semiconductors. Proceedings Annual Meeting Electron Microscopy Society of America, 1991, 49, 850-851.	0.0	0
283	Heteroepitaxial Metal Oxides on Silicon by Laser Ablation. Materials Research Society Symposia Proceedings, 1990, 191, 187.	0.1	7
284	Transmission Electron Microscopy of Excimer Laser Crystallized Amorphous Si Thin Films. Materials Research Society Symposia Proceedings, 1990, 192, 669.	0.1	5
285	Interface Formation and the Heteroepitaxy of ZnSe on Si.. Materials Research Society Symposia Proceedings, 1990, 198, 195.	0.1	3
286	Properties of Interfaces between Superlattice Heterostructures and Uniform Alloy Materials as Realized by Impurity Induced Disordering. Materials Research Society Symposia Proceedings, 1990, 198, 85.	0.1	1
287	In-Situ Growth Of Superconducting YBa 2 Cu 3 O y Films By Pulsed Laser Deposition. Proceedings of SPIE, 1990, 1187, 136.	0.8	3
288	Misfit dislocations in GaAs heteroepitaxy on (001) Si. Journal of Crystal Growth, 1990, 106, 157-165.	0.7	38

#	Article	IF	Citations
289	Excimerâ€laserâ€induced crystallization of hydrogenated amorphous silicon. Applied Physics Letters, 1990, 57, 2222-2224.	1.5	54
290	Thin film backside gettering in n-type (100) Czochralski silicon during simulated CMOS process cycles. Journal of Materials Research, 1989, 4, 623-633.	1.2	10
291	Simple ion milling preparation of ã€ˆ111ã€‰ tungsten tips. Applied Physics Letters, 1989, 54, 1223-1225.	1.5	34
292	Laser patterned desorption within an upflow metalorganic chemical vapor deposition reactor. Applied Surface Science, 1989, 43, 432-438.	3.1	1
293	Microscopic aspects of oxygen precipitation in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 11-17.	1.7	18
294	On the structure of small palladium particles. Scripta Metallurgica, 1989, 23, 1555-1558.	1.2	8
295	High-resolution transmission electron microscopy of 60[ddot] dislocations in si-GaAs. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1989, 59, 1045-1058.	0.8	26
296	Applications of In-Situ UHV and High Resolution Tem to the Study of Small Particles. Materials Research Society Symposia Proceedings, 1989, 139, 81.	0.1	1
297	Very Thin 2D GaAs Films on Si During the Early Stages of Growth by MBE. Materials Research Society Symposia Proceedings, 1989, 159, 15.	0.1	3
298	Xps Analysis of Y-Ba-Cu-O and Zr-O Thin Films and Interfaces with Silicon Substrates. Materials Research Society Symposia Proceedings, 1989, 169, 1005.	0.1	3
299	HREM at orthogonal projections of GaAs islands on silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 586-587.	0.0	0
300	The effect of a Ga prelayer on the beginning of GaAs epitaxy on Si. Journal of Applied Physics, 1988, 64, 3472-3475.	1.1	28
301	Structure of the (100) GaAs on GaP interface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1310.	1.6	4
302	Effects of heavy boron doping upon oxygen precipitation in Czochralski silicon. Journal of Applied Physics, 1988, 64, 4454-4465.	1.1	31
303	Gradedâ€thickness samples for molecular beam epitaxial growth studies of GaAs/Si heteroepitaxy. Applied Physics Letters, 1988, 52, 1779-1781.	1.5	27
304	Layer disordering of GaAsâ€AlGaAs superlattices by diffusion of laserâ€incorporated Si. Journal of Applied Physics, 1988, 64, 3439-3444.	1.1	10
305	Preparation of oriented Biâ€Caâ€Srâ€Cuâ€O thin films using pulsed laser deposition. Applied Physics Letters, 1988, 53, 337-339.	1.5	76
306	Initial Stages of GaAs Epitaxy on Si. Materials Research Society Symposia Proceedings, 1988, 116, 33.	0.1	15

#	Article	IF	Citations
307	The Influence of Substrate Surface Chemistry on GaAs - on - Si Growth. Materials Research Society Symposia Proceedings, 1988, 116, 51.	0.1	4
308	Lattice Mismatch Effects in Gaas Epitaxy on Si and GaP. Materials Research Society Symposia Proceedings, 1988, 122, 21.	0.1	7
309	Precipitation of hydrogen in crystalline silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1988, 46, 476-477.	0.0	1
310	Reactive interface formationâ€"Pt/SiâŒ©111âŒª: Nucleation and morphology. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1039.	1.6	7
311	Ion milled tips for scanning tunneling microscopy. Applied Physics Letters, 1987, 50, 696-698.	1.5	83
312	Engineered Schottky barrier diodes for the modification and control of Schottky barrier heights. Journal of Applied Physics, 1987, 61, 5159-5169.	1.1	59
313	Study of Initial Stages of Heteroepitaxy Using Graded Thickness Samples. Materials Research Society Symposia Proceedings, 1987, 102, 437.	0.1	0
314	Defects in single-crystal silicon induced by hydrogenation. Physical Review B, 1987, 35, 4166-4169.	1.1	432
315	Initial stages of epitaxial growth of GaAs on (100) silicon. Journal of Applied Physics, 1987, 61, 1856-1859.	1.1	148
316	Effects of boron concentration upon oxygen precipitation in CZ silicon. Journal of Crystal Growth, 1987, 85, 91-96.	0.7	10
317	Interface structure in heteroepitaxial CdTe on GaAs(100). Surface Science, 1986, 168, 564-570.	0.8	62
318	Thermodynamic and kinetic considerations on the equilibrium shape for thermally induced microdefects in Czochralski silicon. Journal of Applied Physics, 1986, 59, 3255-3266.	1.1	96
319	Current transport mechanisms in GaAs/AlAs tunnel structures grown by metalâ€"organic chemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 988.	1.6	14
320	Effectiveness of CVD thin Film Backside Gettering and Its Interaction with Intrinsic Gettering. Materials Research Society Symposia Proceedings, 1986, 71, 33.	0.1	4
321	Summary Abstract: High resolution electron microscopy of CaF2/silicon interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 1121.	1.6	34
322	HgTeâ€"CdTe superlattices grown on lattice-mismatched GaAs substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 1306.	1.6	16
323	Interaction Between Deposited Film Extrinsic Gettering and Intrinsic Gettering in CZ Silicon During Simulated CMOS Process Cycles. Materials Research Society Symposia Proceedings, 1985, 59, 353.	0.1	2
324	Crystal orientation dependence of the electrical transport and lattice structure of zinc selenide films grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1985, 58, 1548-1553.	1.1	31

#	Article	IF	Citations
325	Resonant tunneling in GaAs/AlAs heterostructures grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1985, 46, 285-287.	1.5	61
326	Interface effects in amorphous silicon/nitride multilayers. Journal of Non-Crystalline Solids, 1985, 77-78, 995-998.	1.5	23
327	Lattice structure at ZnSeî—¸GaAs heterojunction interfaces prepared by organometallic chemical vapor deposition. Thin Solid Films, 1983, 104, 133-143.	0.8	45
328	Structure of thermally induced microdefects in Czochralski silicon after highâ€temperature annealing. Applied Physics Letters, 1983, 43, 1051-1053.	1.5	63
329	Structural characterization of lowâ€defectâ€density silicon on sapphire. Journal of Applied Physics, 1983, 54, 4414-4420.	1.1	12
330	Interface properties of n-ZnSeâ€“p-Ge heterojunctions grown by organometallic chemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1983, 1, 656.	1.6	16
331	Structure of Thermally-Induced Microdefects in Czochralski Silicon. Materials Research Society Symposia Proceedings, 1983, 31, 153.	0.1	15
332	Faultâ€free silicon at the silicon/sapphire interface. Applied Physics Letters, 1982, 41, 371-373.	1.5	53
333	Crystalline Particles in Thermally Grown Silicon Dioxide. Materials Research Society Symposia Proceedings, 1982, 14, 201.	0.1	0
334	Lattice Structure at ZnSe-GaAs Heterojunction Interfaces Prepared by Organometallic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1982, 18, 133.	0.1	0
335	High-resolution lattice imaging of cadmium telluride. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1982, 45, 693-711.	0.8	22
336	Imaging of interfaces in semiconductor materials using high resolution transmission electron microscopy. Ultramicroscopy, 1982, 9, 215-219.	0.8	2
337	Dynamic observation of defect annealing in CdTe at lattice resolution. Nature, 1982, 298, 127-131.	13.7	55
338	Native tellurium dioxide layer on cadmium telluride: A highâ€resolution electron microscopy study. Applied Physics Letters, 1981, 39, 951-953.	1.5	33
339	Atomic motion on the surface of a cadmium telluride single crystal. Nature, 1981, 290, 386-388.	13.7	62
340	Imaging of the silicon on sapphire interface by highâ€resolution transmission electron microscopy. Applied Physics Letters, 1981, 38, 439-441.	1.5	35
341	High Resolution Imaging of Semiconductor Interfaces. Proceedings Annual Meeting Electron Microscopy Society of America, 1981, 39, 124-127.	0.0	1
342	Lattice Imaging of Heteroepitaxial Silicon on Sapphire. Proceedings Annual Meeting Electron Microscopy Society of America, 1981, 39, 128-129.	0.0	0

#	Article	IF	Citations
343	Silicon-Sapphire Interface: A High Resolution Electron Microscopy Study. Materials Research Society Symposia Proceedings, 1980, 2, 285.	0.1	1
344	Imaging of Defects in Cadmium Telluride using High Resolution Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 1980, 2, 503.	0.1	1
345	Reduction of GaAs diode laser spontaneous emission. Applied Physics Letters, 1980, 37, 10-12.	1.5	4
346	Integrated output power detection for AlGaAs laser array. IEEE Journal of Quantum Electronics, 1980, 16, 502-504.	1.0	4
347	Lateral mode stabilization of diode lasers by means of apertured facet reflectors. IEEE Journal of Quantum Electronics, 1979, 15, 1205-1207.	1.0	7
348	Temperature dependence of thin-film ferromagnetic resonance linewidths. Solid State Communications, 1976, 18, 521-522.	0.9	5
349	Field effect and localization in InGaN/GaN quantum wells. , 0, , .		0
350	Microstructure of In/sub x/Ga/sub 1-x/N thick epitaxial layers. , 0, , .		0
351	Interface atomic arrangement between the nitride semiconductor and silicon. , 0, , .		0
352	Growth-direction dependence of optical properties in epitaxially laterally overgrown GaN. , 0, , .		0
353	Atomic Arrangement at the AlN/Si(110) Interface. Applied Physics Express, 0, 1, 061104.	1.1	21
354	Misfit Strain Relaxation by Stacking Fault Generation in InGaN Quantum Wells Grown onm-Plane GaN. Applied Physics Express, 0, 2, 041002.	1.1	64